

ABSTRACT OF THE DISCLOSURE

One aspect of the present invention relates to a method for making a dual damascene pattern in an insulative layer in a single etch process involving providing a wafer having at least one insulative layer formed thereon; depositing a first photoresist layer over the at least one insulative layer; patterning a first image into the first photoresist layer; curing the first patterned photoresist layer; depositing a second photoresist layer over the first patterned photoresist layer; patterning a second image into the second photoresist layer; and etching the at least one insulative layer through the first patterned photoresist layer and the second patterned photoresist layer simultaneously in the single etch process.